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August 2014

## FDPF045N10A

# N-Channel PowerTrench<sup>®</sup> MOSFET 100 V, 67 A, 4.5 m $\Omega$

#### **Features**

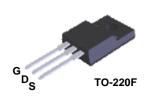
- $R_{DS(on)} = 3.7 \text{ m}\Omega$  ( Typ.)@  $V_{GS} = 10 \text{ V}$ ,  $I_D = 67 \text{ A}$
- · Fast Switching Speed
- Low Gate Charge, Q<sub>G</sub> = 57 nC(Typ.)
- $\bullet$  High Performance Trench Technology for Extremely Low  $R_{\mbox{\scriptsize DS(on)}}$
- High Power and Current Handling Capability
- RoHS Compliant

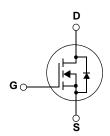
## **Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor<sup>®</sup> s advance PowerTrench<sup>®</sup> process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

#### **Applications**

- Synchronous Rectification for ATX / Server / Telecom PSU
- Motor drives and Uninterruptible Power Supplies
- · Micro Solar Inverter





## MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted\*

Symbol		Parameter		FDPF045N10A	Unit
V <sub>DSS</sub>	Drain to Source Voltage			100	V
V <sub>GSS</sub>	Gate to Source Voltage			±20	V
I- Drain Current		- Continuous (T <sub>C</sub> = 25°C)		67	А
		- Continuous (T <sub>C</sub> = 100°C)	- Continuous (T <sub>C</sub> = 100°C)		A
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	268	Α
E <sub>AS</sub>	Single Pulsed Avalanche En	ergy	(Note 2)	637	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	6.0	V/ns
<b>D</b>	Dower Discipation	$(T_C = 25^{\circ}C)$		43	W
$P_{D}$	Power Dissipation	- Derate above 25°C		0.29	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temp	perature Range		-55 to +175	°С
TL	Maximum Lead Temperature	e for Soldering,1/8" from Case for 5 Sec	onds	300	°C

#### **Thermal Characteristics**

Symbol	Parameter FDPF045N10A		Unit	
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 3.5			
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 62.5		°C/W	

## **Package Marking and Ordering Information**

Device Marking	Device	Package	Packing Method	Reel Size	Tape Width	Quantity
FDPF045N10A	FDPF045N10A	TO-220F	Tube	-	-	50

## **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	100	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C	-	0.06	-	V/°C
1	Zero Gate Voltage Drain Current	$V_{DS} = 80V, V_{GS} = 0V$	-	-	1	μА
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 80V, T_{C} = 150^{\circ}C$	-	-	500	μΑ
I <sub>GSS</sub>	Gate to Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±100	nA

#### On Characteristics

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.0	-	4.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 10V, I_D = 67A$	-	3.7	4.5	mΩ
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = 10V, I_{D} = 67A$	-	127	-	S

### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 50V V 0V	=	3961	5270	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 50V, V_{GS} = 0V$ f = 1MHz		925	1230	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1101112	-	34	-	pF
C <sub>oss</sub> (er)	Energy Releted Output Capacitance	$V_{DS} = 50V, V_{GS} = 0V$	-\	1521	-	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V		-	57	74	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	$V_{GS} = 10V, V_{DS} = 50V$	- \	17	-	nC
Q <sub>gs2</sub>	Gate Charge Threshold to Plateau	I <sub>D</sub> = 100A	-	8	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	13	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1MHz	-	1.9	-	Ω

### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		-	23	56	ns
t <sub>r</sub>		$V_{DD} = 50V, I_{D} = 100A$	-	26	62	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10V$ , $R_{GEN} = 4.7\Omega$	-	50	110	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	-	15	40	ns

#### **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current			-	67	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	268	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_{SD} = 67A$	-	-	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, V <sub>DD</sub> = 50V, I <sub>SD</sub> = 100A	-	75	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	-	120	-	nC

#### Notes:

- Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L = 3mH,  $\rm I_{AS}$  = 20.6A,  $\rm R_G$  = 25 $\Omega$ , Starting  $\rm T_J$  = 25°C
- 3.  $I_{SD} \leq 100 A$ , di/dt  $\leq 200 A/\mu s$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^{\circ}C$
- 4. Essentially Independent of Operating Temperature Typical Characteristics

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

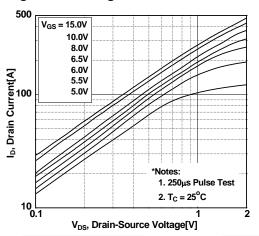


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

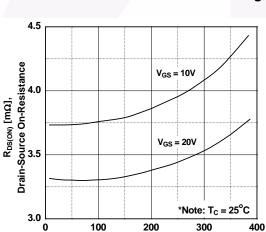


Figure 5. Capacitance Characteristics

ID, Drain Current [A]

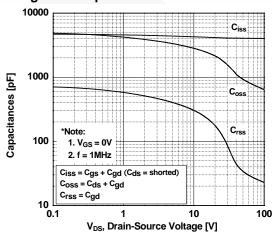


Figure 2. Transfer Characteristics

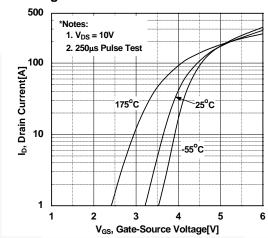


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

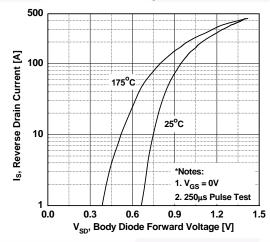
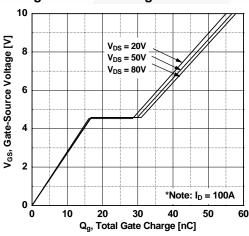


Figure 6. Gate Charge Characteristics



## **Typical Performance Characteristics (Continued)**

Figure 7. Breakdown Voltage Variation vs. Temperature

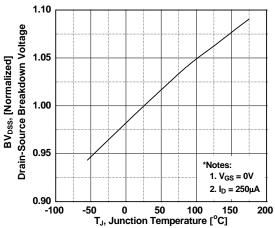


Figure 9. Maximum Safe Operating Area

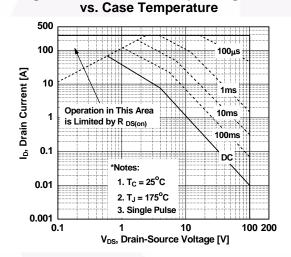


Figure 11. Eoss vs. Drain to Source Voltage

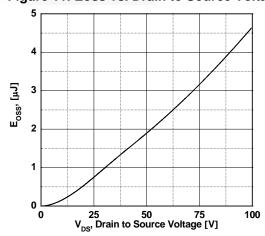


Figure 8. On-Resistance Variation vs. Temperature

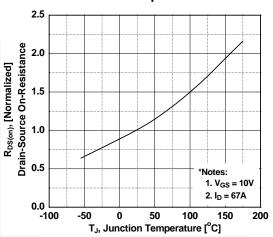
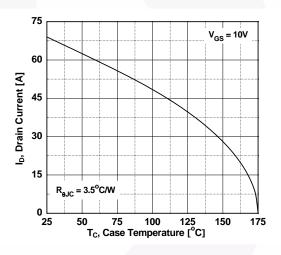
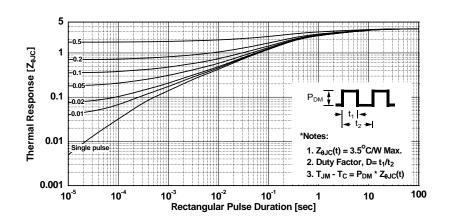


Figure 10. Maximum Drain Current



## **Typical Performance Characteristics** (Continued)

**Figure 12. Transient Thermal Response Curve** 



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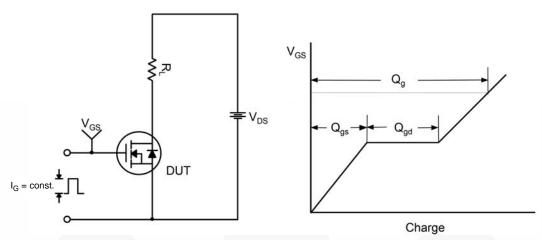


Figure 13. Gate Charge Test Circuit & Waveform

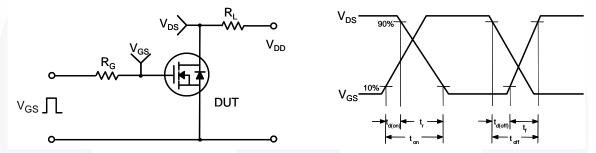


Figure 14. Resistive Switching Test Circuit & Waveforms

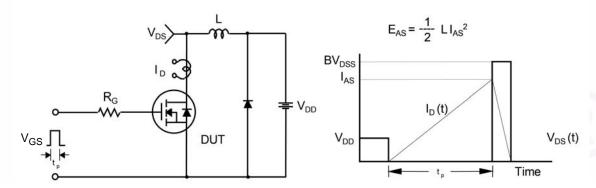


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

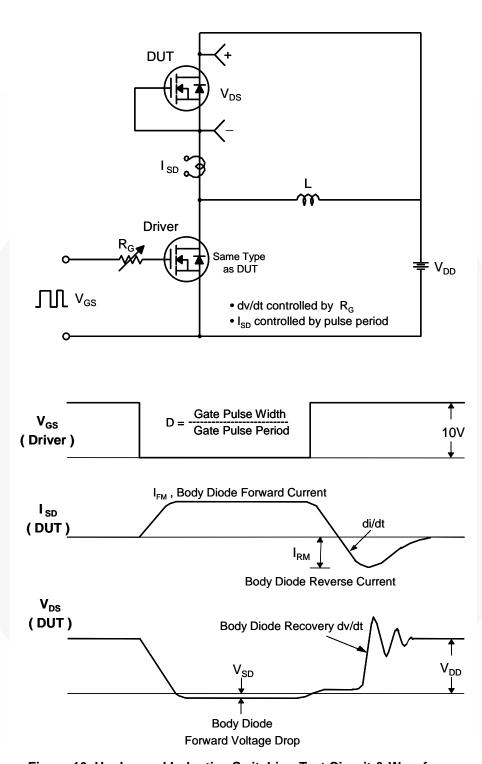


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

#### **Mechanical Dimensions**

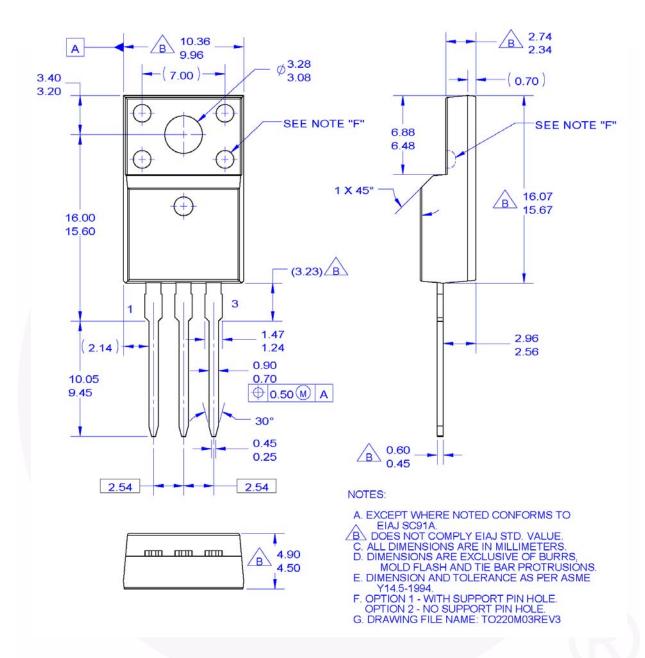


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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